JFW

Docket No.: 42P18252

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

PETER L.D. CHANG

Application No.: 10/816,282

Filed: March 31, 2004

For: **Memory with Split Gate Devices and Method of Fabrication**

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In accordance with the duty of disclosure, enclosed is a copy of IDS Citation Form PTO/SB/08 or PTO-1449, together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). This IDS and IDS Citation Form are being submitted before the mailing of a first Office Action. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Date: 10/26/04

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I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: ~~Mail Stop Missing Parts,~~ Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Conny Willesen 10/29/04

Conny Willesen *Date*

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet	1	of	1

Complete if Known	
Application Number	10/816,282
Filing Date	March 31, 2004
First Named Inventor	Peter L.D. Chang
Art Unit	
Examiner Name	
Attorney Docket Number	42P18252

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		FRIED, David et al., "High-Performance P-Type Independent-Gate FinFETs," IEEE Electron Device Letters, Vol. 25, No. 4, April 2004, pgs. 199-201.	
		FRIED, David et al., "Improved Independent Gate N-Type FinFET Fabrication and Characterization," IEEE Electron Device Letters, Vol. 24, No. 9, Sept. 2003, pgs. 592-594.	
		KUO, Charles et al., "Capacitorless Double-Gate DRAM Cell Design for High Density Applications," IEDM, 2002, pages 843-846.	
		CHAN, Mansun et al., "Recessed-Channel Structure for Fabricating Ultrathin SOI MOSFET with Low Series Resistance," IEEE Electron Device Letters, Vol. 15, No. 1, Jan. 1994, 3	
		OHSAWA, Takashi et al., "Memory Design Using a One-Transistor Gain Cell on SOI," IEEE Jrl of Solid-State Circuits, Vol. 37, No. 11, Nov. 2002, pages 1510-1522.	

Examiner Signature		Date Considered	

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

[1]Applicant's unique citation designation number. [2]Applicant is to place a check mark here if English language Translation is attached.